Bipolar Power Transistors

PNP Silicon

Features

- Epoxy Meets UL 94, V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	40	Vdc	
Collector-Base Voltage	V _{CB}	40	Vdc	
Emitter-Base Voltage	V _{EB}	6.0	Vdc	
Base Current - Continuous	I _B	1.0	Adc	
Collector Current - Continuous	I _C	3.0	Adc	
Collector Current - Peak	I _{CM}	5.0	Adc	
ESD - Human Body Model	НВМ	3B	V	
ESD - Machine Model	MM	С	V	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P _D @ T _A = 25°C (Note 1) Total P _D @ T _A = 25°C (Note 2)	P _D	2.0 0.80	W
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$egin{array}{l} R_{ hetaJA} \ R_{ hetaJA} \end{array}$	64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

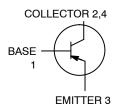
- 1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
- 2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



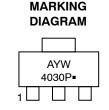
ON Semiconductor®

http://onsemi.com

PNP TRANSISTOR 3.0 AMPERES 40 VOLTS, 2.0 WATTS







A = Assembly Location

' Year

W = Work Week

4030P = Specific Device Code ■ Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NJT4030NT1G	SOT-223	1000 / Tape &
NJV4030NT1G	(Pb-Free)	Reel
NJT4030NT3G	SOT-223	4000 / Tape &
NJV4030NT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			-76		
Collector-Emitter Sustaining Voltage (I _C = 10 mAdc, I _B = 0 Adc)	V _{CEO(sus)}	40	-	-	Vdc
Emitter–Base Voltage ($I_E = 50 \mu Adc$, $I_C = 0 Adc$)	V _{EBO}	6.0	-	-	Vdc
Collector Cutoff Current (V _{CB} = 40 Vdc)	I _{CBO}	-	-	100	nAdc
Emitter Cutoff Current (V _{BE} = 6.0 Vdc)	I _{EBO}	-	-	100	nAdc
ON CHARACTERISTICS (Note 3)					
	V _{CE(sat)}	- - -	- - -	0.150 0.200 0.500	Vdc
Base–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)	V _{BE(sat)}	-	-	1.0	Vdc
Base–Emitter On Voltage ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	V _{BE(on)}	-	-	1.0	Vdc
DC Current Gain ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	220 200 100	- - -	- 400 -	-
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 Vdc, f = 1.0 MHz)	C _{ob}	-	40	-	pF
Input Capacitance (V _{EB} = 5.0 Vdc, f = 1.0 MHz)	C _{ib}	-	130	-	pF
Current-Gain - Bandwidth Product (Note 4) (I _C = 500 mA, V _{CE} = 10 V, F _{test} = 1.0 MHz)	f _T	-	160	-	MHz

^{3.} Pulse Test: Pulse Width \leq 300 $\mu\text{s},$ Duty Cycle \leq 2%.

^{4.} $f_T = |h_{FE}| \cdot f_{test}$

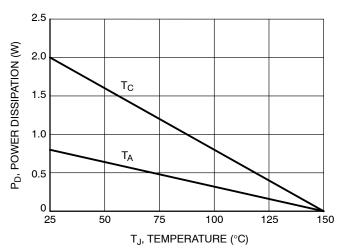


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

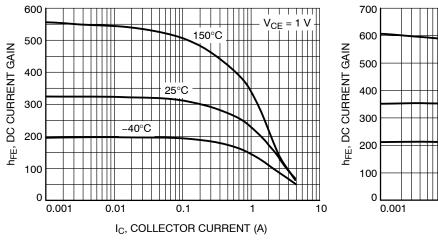


Figure 2. DC Current Gain

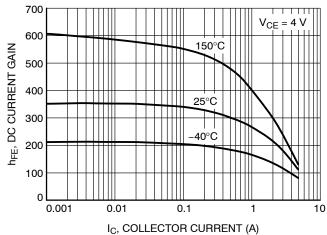


Figure 3. DC Current Gain

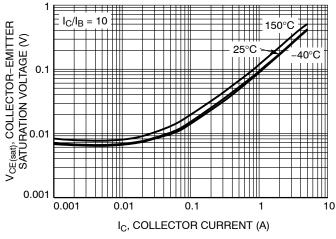


Figure 4. Collector-Emitter Saturation Voltage

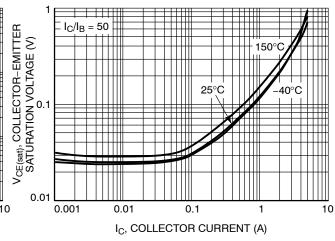


Figure 5. Collector-Emitter Saturation Voltage

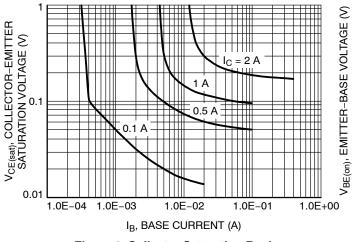


Figure 6. Collector Saturation Region

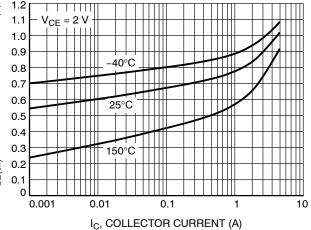


Figure 7. V_{BE(on)} Voltage

TYPICAL CHARACTERISTICS

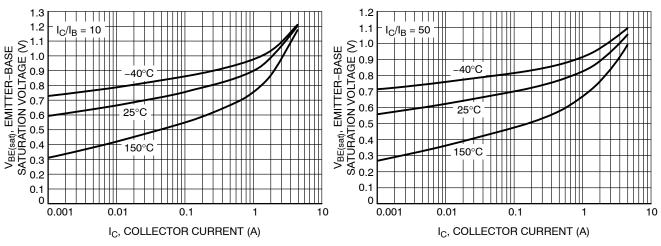


Figure 8. Base-Emitter Saturation Voltage

Figure 9. Base-Emitter Saturation Voltage

 $T_J = 25^{\circ}C$

f_{test} = 1 MHz

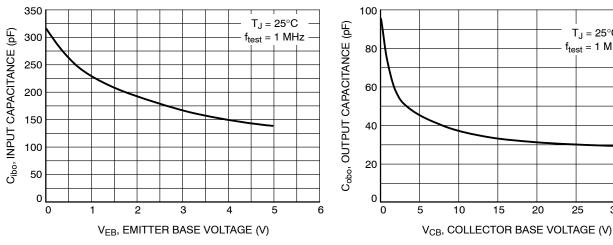


Figure 10. Input Capacitance

Figure 11. Output Capacitance

20

25

30

35

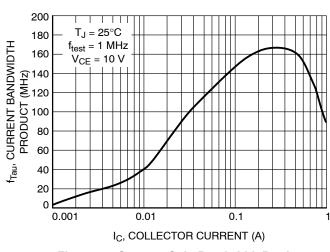


Figure 12. Current-Gain Bandwidth Product

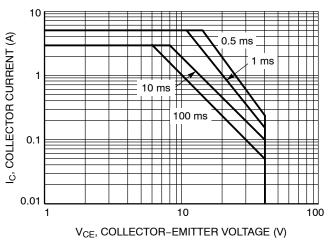
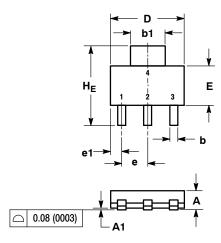
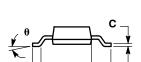


Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE N





- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCH.

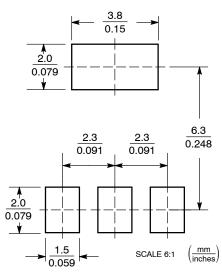
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
O	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
٦	0.20			0.008		
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°		10°	0°	_	10°

STYLE 1:

- PIN 1. BASE
 - COLLECTOR EMITTER

 - COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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